

Day : Friday
Date: 5/17/2002

Time: 17:40:19

PALM INTRANET

Docket	Reg. New	Reg. Amended	Spl. New	Spl. Amended	Rejected	Counted Not
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Regular New Cases

(WARNING: Data Security and Confidentiality Restriction Apply)

Name : GARCIA, JOANNIE

Examiner Number : 76803

Group Art Unit : 2823

Regular New Cases : 17

Oldest New S.N. : Age:

Oldest Effective S.N. : Age:

No.	Appln #	Filing Date	Status	Loc	Chg To Loc	Class	Subclass	Title
1	09/521034	03/08/2000	30	28C1	28X1	438	689.000	ACOUSTIC/ULTRASONIC AGITATION TO REDUCE MICROBUBBLES IN DEVELOPER
2	09/725853	11/30/2000	30	28C1	-	438	462.000	PHOTOMASK INCLUDING AUXILIARY MARK AREA, SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF
3	09/726054	11/30/2000	30	28C1	-	438	128.000	METHOD OF FABRICATING SEMICONDUCTOR DEVICE
4	09/728684	11/30/2000	30	28C1	-	438	687.000	METHOD OF REDUCING ELECTROMIGRATION IN COPPER LINES BY CALCIUM-DOPING COPPER SURFACES IN A CHEMICAL SOLUTION AND SEMICONDUCTOR DEVICE THEREBY FORMED
5	09/727833	12/01/2000	30	28C1	-	438	612.000	METHOD FOR FORMING ANCHORED BOND PADS IN SEMICONDUCTOR DEVICES AND DEVICES FORMED
6	09/735864	12/13/2000	30	28C1	-	438	257.000	NONVOLATILE SEMICONDUCTOR MEMORY DEVICE AND MANUFACTURING METHOD THEREOF
7	09/739733	12/18/2000	30	28C1	-	438	263.000	METHODS TO FORM REDUCED DIMENSION BIT-LINE ISOLATION IN THE MANUFACTURE OF NON-VOLATILE MEMORY DEVICES

8 09/757,514

Repository CF

9	<u>09/764834</u>	01/17/2001	30	2FC1	-	438	243.000	PRODUCTION OF METAL INSULATOR METAL (MIM) STRUCTURES USING ANODIZING PROCESS
10	<u>09/766013</u>	01/18/2001	30	2FC1	-	438	192.000	6F2 TRENCH EDAM CELL WITH DOUBLE-GATED VERTICAL MOSFET AND SELF-ALIGNED STI
11	<u>09/764333</u>	01/19/2001	30	2FC1	-	438	257.000	METHOD FOR MAKING AN EMBEDDED MEMORY MOS
12	<u>09/764334</u>	01/19/2001	30	2FC1	-	438	258.000	METHOD FOR MAKING AN EMBEDDED MEMORY MOS
13	<u>09/767263</u>	01/23/2001	30	2FC1	-	438	255.000	METHOD FOR FABRICATING SEMICONDUCTOR CAPACITOR
14	<u>09/775713</u>	02/05/2001	30	2FC1	-	438	239.000	METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE INCLUDING A STEP OF FORMING A SILICIDE LAYER, AND SEMICONDUCTOR DEVICE MANUFACTURED THEREBY
15	<u>09/796213</u>	02/28/2001	30	2FC1	-	438	243.000	METHOD FOR INCREASING THE CAPACITANCE IN A STORAGE TRENCH AND TRENCH CAPACITOR HAVING INCREASED CAPACITANCE
16	<u>09/798923</u>	03/06/2001	30	2FC1	-	438	257.000	SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME
17	<u>10/026010</u>	12/21/2001	30	2FC1	-	455	001.000	PORTABLE COMMUNICATION DEVICE THAT MAY PERMIT ONE WIRELESS NETWORK TO COMMUNICATE WITH ANOTHER WIRELESS NETWORKS AND METHOD THEREFOR

Docket	Reg. New	Reg. Amended	Spl. New	Spl. Amended	Rejected	Counted Not
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